˜Yت / Descriptions

SOT-89 NPN Silicon NPN transistor in a SOT-89 Plastic Package.

◕ È / Features

, , 2SB1386

Low $V_{CE(sat)}$, excellent DC current gain , complements the 2SB1386.

४ ي / Applications

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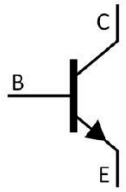
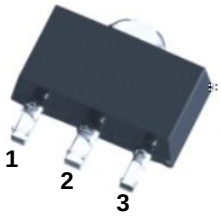
Strobe flash applications, general power amplifier applications.

Л ف ̃ ̃ ̣ ع / Equivalent Circuit



ã ⅄ ʊ˜ / Pinning



PIN1 Base PIN 2 Collector PIN 3 Emitter

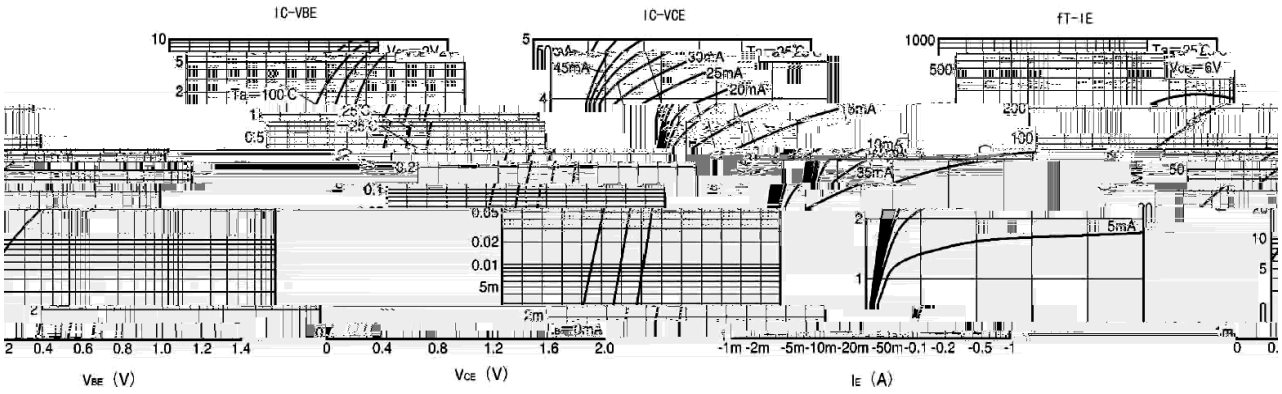
Łˌ ʜ ̇ / Marking

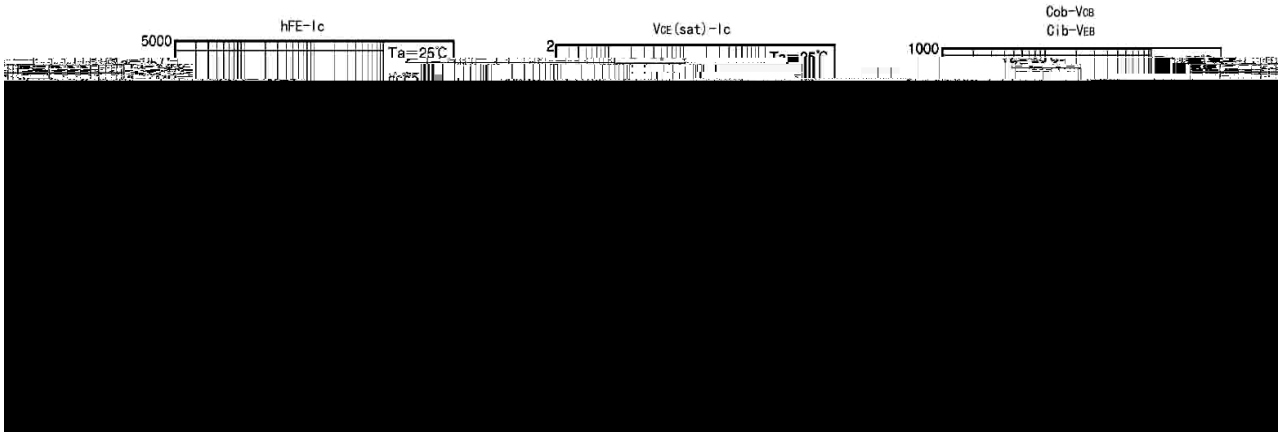
h_{FE} Classifications Symbol	Q	R
h_{FE} Range	120 270	180 390
Marking	HAHQ‡	HAHR ⁑

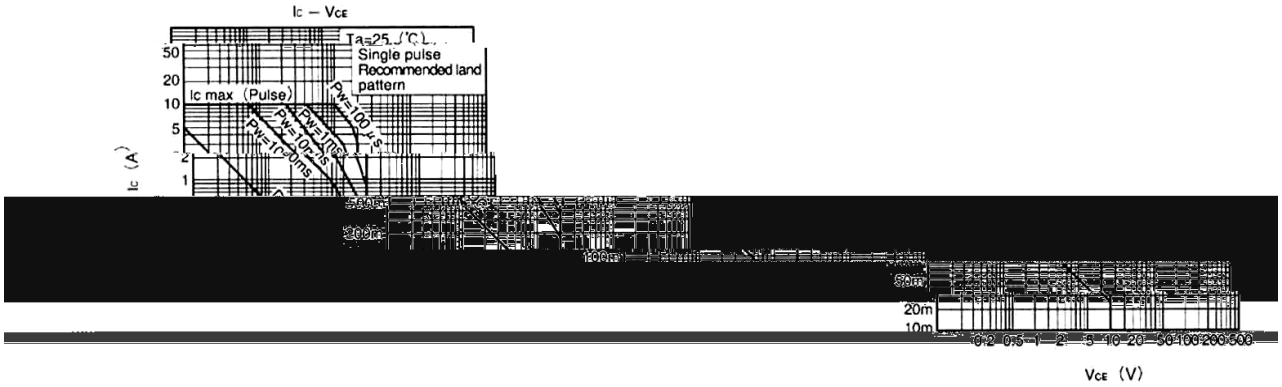
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	50	V
Collector to Emitter Voltage	V_{CEO}	20	V
Emitter to Base Voltage	V_{EBO}	6.0	V
Collector Current-Continuous	I_C	5.0	A
Collector Current -Continuous(Pulse)	I_{CP}	10	A
Collector Power Dissipation	P_C	0.5	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBO}	I_C=50μA I_E=				

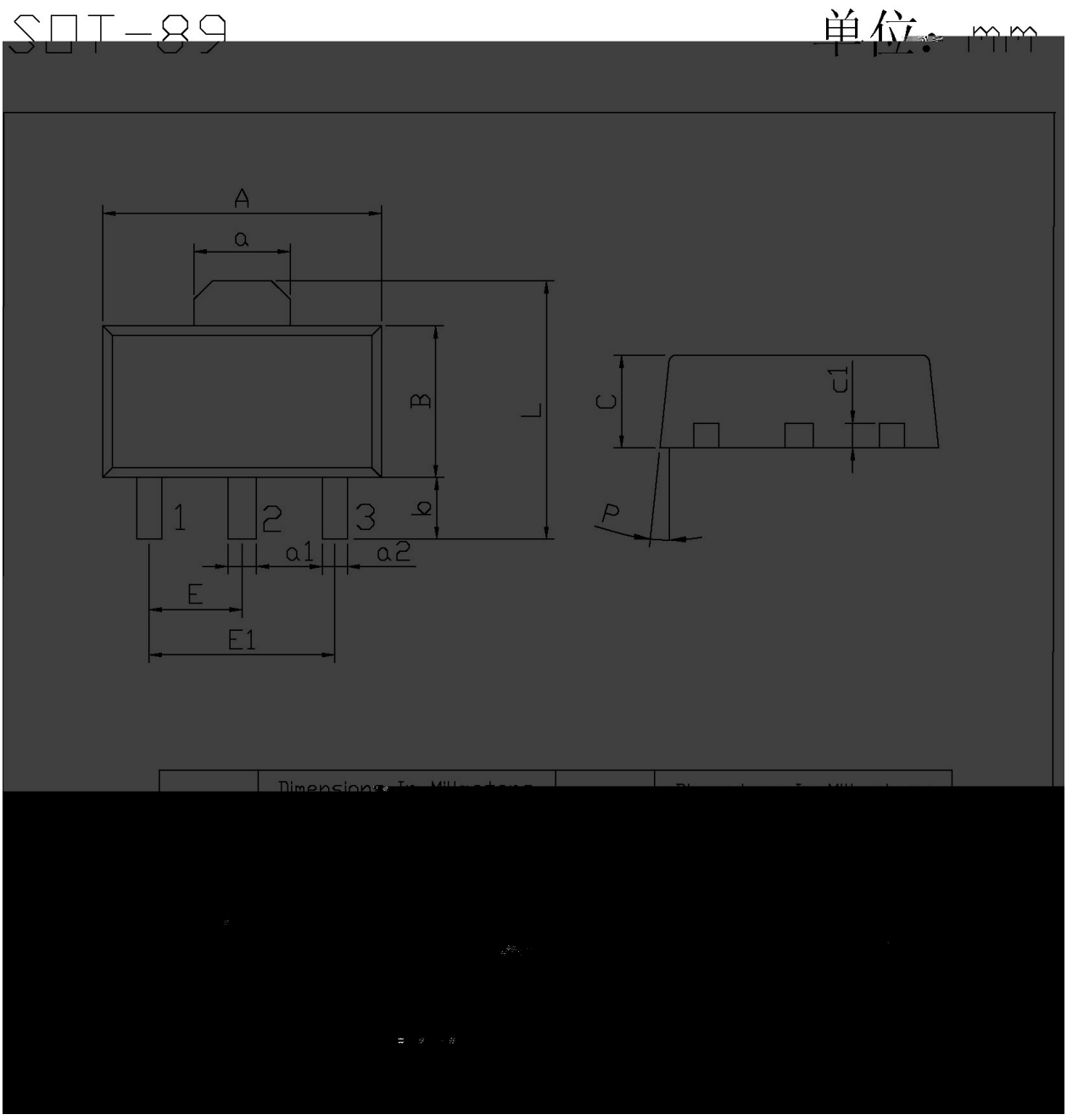
⁝ ƎẬ´E ⅵ ƒ / Electrical Characteristic Curve



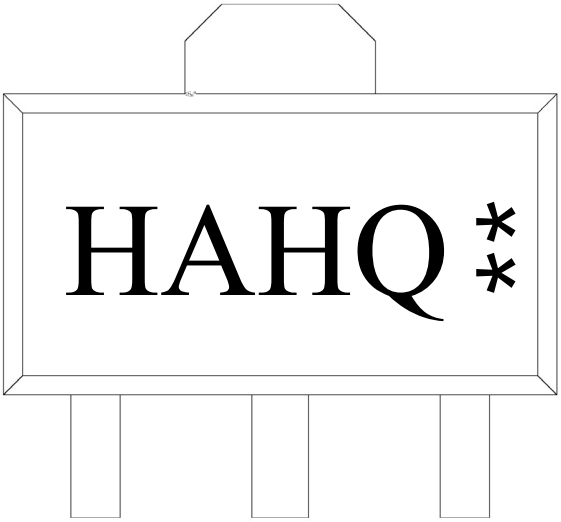




ᵘ ĖÒĻ ʃ / Package Dimensions



Ł. Ł'Ω / Marking Instructions



H

AH

Q h_{FE}

**

Note:

H: Company Code.

AH: Product Type.

Q h_{FE} Classifications Symbol

**: Lot No. Code, code change with Lot No.

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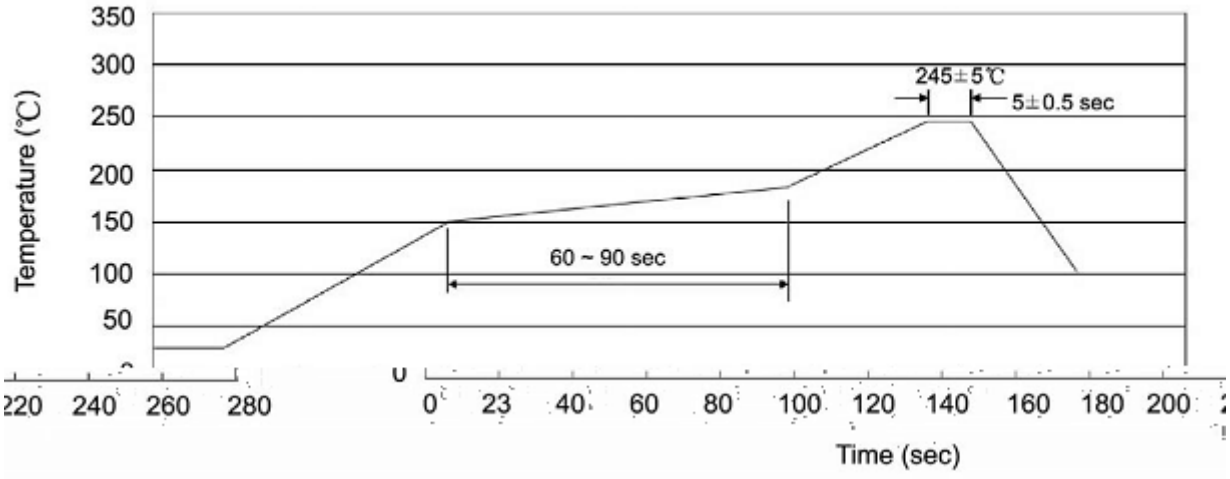

1	25 150	60 90sec;	Note:	
2	245±5	5±0.5sec;	1.Preheating:25~150	, Time:60~90sec.
3	2 10 /sec.		2.Peak Temp.:245±5	, Duration:5±0.5sec.
			3. Cooling Speed: 2~10 /sec.	

⅃ ǖ ɑ ˉ ˋY Ţ / Resistance to Soldering Heat Test Conditions

260±5 10±1 sec. Temp.:260±5 Time:10±1 sec

ɒ ᴇ ᴄ— / Packaging SPEC.

/ REEL

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm^3)		
	Units/Reel 只/卷盘	Reels/Inner Box 卷盘/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Reel	Inner Box 盒	Outer Box 箱
SOT-89	1,000	7	7,000	8	56,000	7 ×12	180×120×180	385×257×392

ä ɤ ʅ ̈Ω / Notices